



Amendments to the Claims:

This listing of claims replaces all prior versions and listings of claims in the application:

Listing of Claims:

1. (Currently Amended) A display device in which a thin film transistor is disposed on an insulative substrate, said thin film transistor comprising:
 - a first gate electrode; a gate insulating film; a semiconductor film which is formed on said gate insulating film and which has a channel;
 - an insulating film;
 - a reflective display electrode connected to a source which is formed in said semiconductor film, said display electrode being elongated so as to extend above said channel of said thin film transistor, and
 - a second gate electrode formed between said first gate electrode and said display electrode,

wherein the first gate electrode comprises a double gate structure divided below the channel,
wherein the second gate electrode covers a larger area than the first gate electrode, and
wherein the second gate electrode comprises a single gate structure.
2. (Currently Amended) A display device in which a thin film transistor is disposed on an insulative substrate, said thin film transistor comprising:
 - a first gate electrode; a gate insulating film; a semiconductor film which is formed on said gate insulating film and which has a channel;
 - an insulating film;
 - a reflective display electrode connected to a source which is formed in said semiconductor film, said display electrode being elongated so as to extend above said channel of said thin film transistor; and

a second gate electrode formed between said first gate electrode and said display electrode,

wherein the first gate electrode comprises a double gate structure divided below the channel;

wherein said second gate electrode is connected with said first gate electrode; [[and]]
wherein the second gate electrode covers a larger area than the first gate electrode; and
wherein the second gate electrode comprises a single gate structure.

3. (Original) A display device according to claim 2, wherein said second gate electrode is formed so as to be faced with said first gate electrode through said insulating film.

4. (Original) A display device according to claim 3, wherein said display electrode is rectangular.

5. (Original) A display device according to claim 1, wherein said channel is covered with a stopper insulating film.

6. (Original) A display device according to claim 5, wherein said stopper insulating film is made of an SiO₂ film.

7. (Original) A display device according to claim 5, wherein said stopper insulating film is made of a two-layered film of SiN and organic film.

8-10. (Canceled)

11. (Currently Amended) A display device according to claim [[10]] 1, wherein said reflective display electrode is made of Al-Nd alloy.

12. (Original) A display device according to claim 1, wherein said display electrode is an electrode used in a liquid display device.

13. (Original) A display device according to claim 1, wherein a light emitting layer is formed on said display electrode, and said display electrode used in an organic electro luminescent device.

14. (Previously Presented) A display device according to claim 1, wherein said thin film transistor further comprises:

a holding capacitance electrode;

wherein a capacitance electrode connected to the source region and the holding capacitance electrode are arranged relative to each other to constitute a capacitance; and

wherein the holding capacitance electrode is made of a same material as the first gate electrode.

15. (Currently Amended) A display device according to claim 2, wherein a light ~~emitting~~ emitting layer is formed on said display electrode, and said display electrode used in an organic electro luminescent device.

16. (Previously Presented) A display device according to claim 2, wherein said thin film transistor further comprises:

a holding capacitance electrode;

wherein a capacitance electrode connected to the source region and the holding capacitance electrode are arranged relative to each other to constitute a capacitance; and

wherein the holding capacitance electrode is made of a same material as the first gate electrode.

17. (Currently Amended) A display device comprising:
an insulative substrate;

a thin film transistor including a first gate electrode, a second gate electrode, a gate insulating film and a channel region;

a reflective display electrode connected to one of a source region of the thin film transistor and a drain region of the thin film transistor, said display electrode being extended above the channel region of the thin film transistor;

[[an]] the second gate electrode provided between the channel region of the thin film transistor and the display electrode,

wherein the second gate electrode is connected to the first gate electrode; [[and]]

wherein the first gate electrode comprises a double gate structure divided below the channel region;

wherein the second gate electrode covers a larger area than the first gate electrode; and
wherein the second gate electrode comprises a single gate structure.

18. (Canceled)

19. (Original) A display device according to claim 17, wherein a light emitting layer is formed on said display electrode, and said display electrode used in an organic electro luminescent device.

20. (Previously Presented) A display device according to claim 17, further comprising:

a holding capacitance electrode;

wherein a capacitance electrode connected to the source region and the holding capacitance electrode are arranged relative to each other to constitute a capacitance; and

wherein the holding capacitance electrode is made of a same material as the first gate electrode.

21. (Currently Amended) A display device comprising:
an insulative substrate;

a thin film transistor including a first gate electrode, a second gate electrode, a gate insulating film and a channel region;

a reflective display electrode connected to one of a source region of the thin film transistor and a drain region of the thin film transistor, said display electrode being extended above the channel region of the thin film transistor;

wherein the second gate [[an]] electrode is provided between the channel region of the thin film transistor and the display electrode,

wherein a gate voltage is applied to the second gate electrode, [[and]]

wherein the first gate electrode comprises a double gate structure divided below the channel region,

wherein the second gate electrode covers a larger area than the first gate electrode, and
wherein the second gate electrode comprises a single gate structure.

22. (Canceled)

23. (Currently Amended) A display device according to claim [[22]] 21, wherein a light emitting layer is formed on said display electrode, and said display electrode used in an organic electro luminescent device.

24. (Currently Amended) A display device according to claim [[22]] 21, further comprising:

a holding capacitance electrode line;

wherein a capacitance electrode connected to the source region and the holding electrode line are arranged relative to each other to constitute a capacitance; and

wherein the holding capacitance electrode is made of a same material as the first gate electrode.

25. (New) A display device according to claim 1, wherein the double gate structure comprises two substantially parallel members that extend from a gate signal line.

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Serial No. : 10/758,321
Filed : January 15, 2004
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Attorney's Docket No.: 10417-025002 / S21-
121248M/SW

26. (New) A display device according to claim 25 wherein the single gate structure comprises a single element that covers both of the substantially parallel members.